DPS2014 TIMETABLE(tentative)

November 27

Time	Program	Session
8:00 8:10 8:20 8:30 8:40 8:50	Registration	
9:00	Opening Remark (Hayashi) Young Award, NIshizawa Award (Nakano)	
9:10 9:20 9:30	A-1 <Invited> Dr. Itaru Yanagi (Hitachi Ltd.) "A novel method for fabricating nanopores with diameters of sub-1 nm to 3 nm"	Session A Plasma Processes for New Applications
9:40 9:50 10:00	A-2 <Invited> Dr. Meng-Jiy Wang (National Taiwan University of Science and Technology) "Plasma surface modifications for modulating drug release and cell proliferation"	Session A
10:10 10:20 10:30	A-3 <Invited> Dr. Rui Zhang (Univ. of Tokyo) "MOS interface passivation of Ge MOSFETs by plasma post oxidation"	Session A
10:40	Break	
10:50 11:00	B-1 M. Matsui, "Analysis of surface reaction layers formed by Si_3N_4 etching by pulsed microwave plasma"	Session B Etching and Surface Reaction
11:10 11:20	B-2 T. Sasaki, "Highly selective etching of $LaAlSiO_x$ to Si using $C_4F_8/Ar/H_2$ plasma"	Session B
11:30 11:40	B-3 Hu Li, "Etching characteristics of transparent conducting oxides by methane-based plasmas"	Session B
11:50 12:00	B-4 K. Karahashi, "Etching reactions of magnetic materials by CO cluster beams"	Session B
12:10 12:20	B-5 K. Eriguchi, "A model for plasma-induced latent defects in three-dimensional structures and its application to parameter variation analysis of FinFETs"	Session B
12:30 12:40 12:50 13:00 13:10 13:20 13:30	Lunch	
13:40 13:50 14:00	C-1 <Invited> Dr. Keiji Nakayama (Institute of Mesotechnology) "Atmospheric pressure plasma generated in a gap of dry and oil lubricated sliding	Session C Plasma Monitoring and Simulation
14:10 14:20 14:30	C-2 <Invited> Dr. Laxminarayan Raja (Univ. of Texas at Austin) "Computational simulations of streamer discharges for reactive plasma applications at atmospheric pressures"	Session C
14:40 14:50	C-3 A. Pandey, "Time-resolved curling-probe measurement of electron density in pulsed discharge"	Session C
15:00 15:10	C-4 N. Kuboi, "Prediction of Plasma-Induced Damage Distribution during Silicon Nitride Etching Using Advanced 3D Voxel Model"	Session C
15:20 15:30	C-5 T. Kawanabe, "Controlling ashing rate distribution by introducing additional gas flow in a 450-mm-wafer ashing reactor"	Session C
15:40 15:50	Break	
16:00 16:10 16:20	D-1 <Invited> Dr. Hironobu Sato (EIDEC) "Sub-10nm directed self-assembly lithography using high chi block copolymers"	Session D Dry Etching Technology for Advanced Patterning
16:30 16:40	D-2 L. Azarnouche, "Interactions between plasma and organosilicon polymers for directed self-assembly patterning applications"	Session D
16:50 17:00	D-3 Yan Zhang, "Surface Modifications of Photoresist Polymers under Photon Irradiations Emitted from HBr Plasma"	Session D
17:10 17:20	D-4 J.H. Liao, "Etch Challenges for Metal Hard Mask Open for 14 nm Node"	Session D
17:30 17:40	D-5 O. Ros, "Cure free plasma processes for improved gate patterning and LWR for 14nm FDSOI technologies"	Session D
17:50 18:00		
18:10 18:20 18:30 18:40 18:50 19:00 19:10 19:20 19:30 19:40 19:50 20:00	Banquet	
20:10 20:20 20:30		

November 28

Time	Program	Session
8:00 8:10 8:20 8:30 8:40 8:50	Registration	
9:00 9:10 9:20	E-1 <Invited> Dr. Yasuaki Ishikawa (NAIST) "ALD's oxidant effect on characteristics as an oxide dielectric"	Session E CVD/PVD/ALD
9:30 9:40 9:50	E-2 <Invited> Dr. Paul Poodt (TNO/Holst Centre) "Spatial Atomic Layer Deposition for large-area and flexible electronics"	Session E
10:00 10:10	E-3 M. Noma, "Effects of ion energy on surface and mechanical properties of BN films formed by a reactive plasma-assisted coating method"	Session E
10:20 10:30	E-4 S. Nunomura, "In-situ monitoring of carrier transport in semiconductor active layer under plasma processing"	Session E
10:40 10:50	E-5 Y. Setsuhara, "Process Controllability of ICP-Enhanced Reactive Sputter Deposition for Low-Temperature Formation of IGZO TFT"	Session E
11:00	Break	
11:10 11:20 11:30 11:40 11:50 12:00 12:10 12:20 12:30 12:40	Poster	
12:50 13:00 13:10 13:20 13:30 13:40	Lunch	
13:50 14:00	F-1 T. Ikeda, "Experimental evidence of layout-dependent low-k damage during plasma processing -Role of	Session F Plasma Induced Damage
14:10 14:20	F-2 M. Fukasawa, "Systematic comparison of various analytical techniques for evaluating plasma-induced damage	Session F
14:30 14:40	F-3 T. Iwai, "Low-temperature microwave repairing for plasma-induced local defect structures near Si substrate surface"	Session F
14:50 15:00	F-4 Z. Liu, "Damage-formations in GaN processed at high temperatures"	Session F
15:10 15:20	F-5 T. Shigetoshi, "Control of $Si-SiO_2$ Interface Defects Generation during Thin Dielectric Film Etching Using $CH_xF_y/Ar/O_2$ Plasma"	Session F
15:30 15:40	Break	
15:50 16:00 16:10	G-1 <Invited> Dr. Shahid Rauf (Applied Materials Inc.) "Atomic precision etch for semiconductor manufacturing"	Session G Atomic Layer Etching
16:20 16:30 16:40	G-2 <Invited> Dr. Geun Young Yeom (Sungkyunkwan University) "Application of atomic layer etching for Si-based devices"	Session G
16:50 17:00	G-3 A. Agarwal, "Modeling of Low Electron Temperature Plasmas to Enable Atomic Layer Etching"	Session G
17:10 17:20	G-4 T. Lill, "Plasma-Enhanced Adsorption for Atomic Layer Etch of Silicon"	Session G
17:30	Closing Remark (Okumura)	
17:40 17:50 18:00		